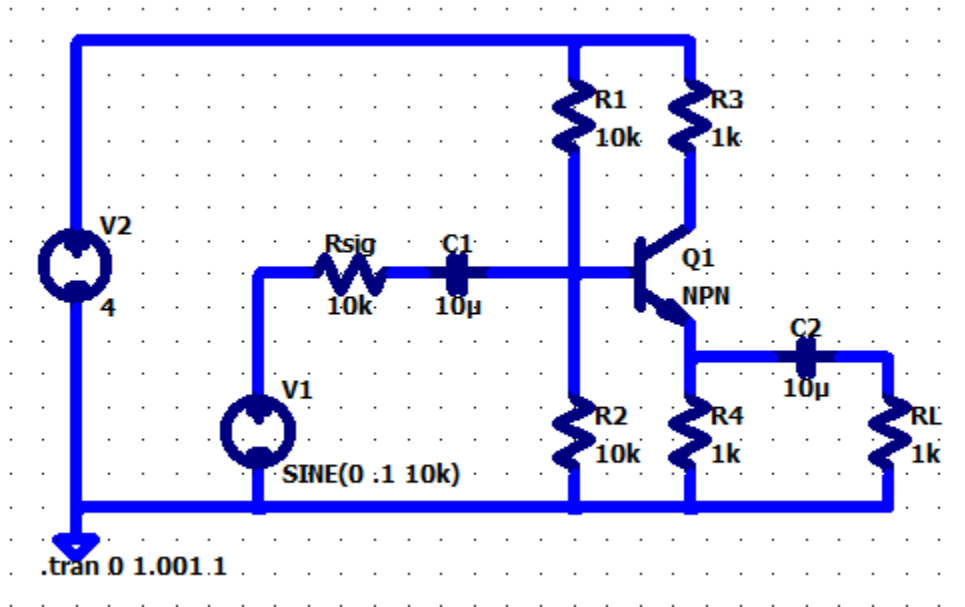


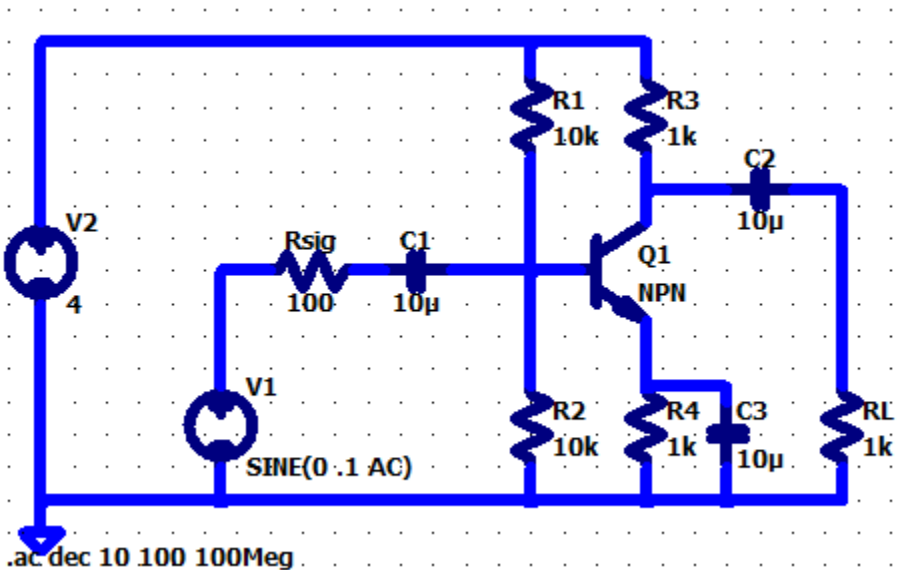
Pre Lab Exercise 2:

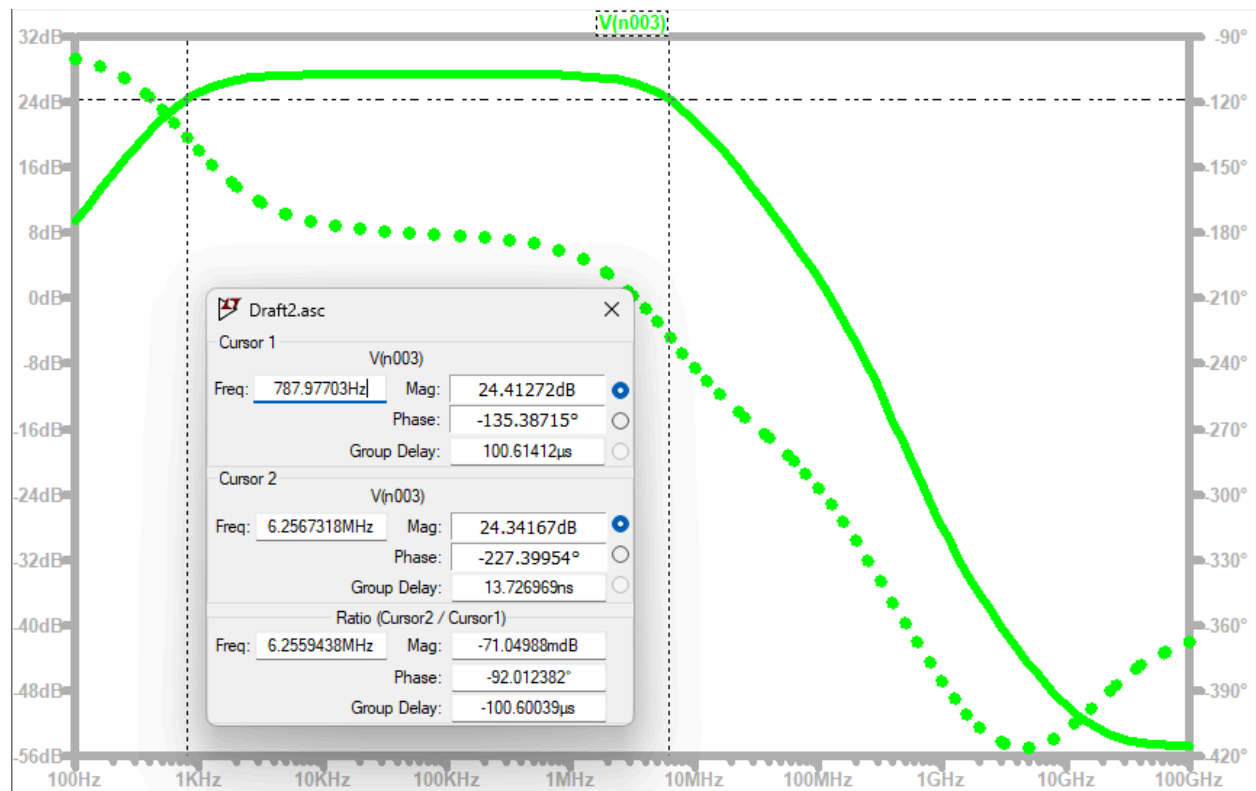
1. Implement the Exercise 3 circuit (shown below) in PSpice (common C amplifier), setting $V_{CC} = 4\text{ V}$, $R_{Sig} = 10\text{ k}\Omega$ and $R_L = 1\text{ k}\Omega$. Set the source to a 10 kHz, 0.2 Vpp sinusoidal voltage signal. Identify the passband voltage gain (AVOC).



$$AVOC = V_{out}/V_{in} = 0.3 = -10.45\text{dB}$$

2. Implement the Exercise 4 circuit (shown below) in PSpice (common E amplifier), setting $V_{CC} = 4\text{ V}$, $R_{Sig} = 100\text{ }\Omega$ and $R_L = 1\text{ k}\Omega$, and run an AC sweep. Identify the passband gain (AVOC) and the low frequency and high frequency cutoff values (-3-dB points).





AVOC=27.4dB

Low cutoff=788Hz

High cutoff=6.35MHz

Exercise 2:

For the PSpice simulations, the transistors are Q2N2222 and for the experimental portion, the transistors are PN2222.

- 1) Build the circuit shown below, using $V_{CC} = 4.0\text{ V}$.
- 2) Measure DC quantities V_{BE} , V_{CE} , I_B , I_C , and I_E using the multimeter on the bench. The bench multimeter has a better input impedance than the Mobile Studio or Discovery Board. To measure I_B , use KCL with regard to I_{R1} and I_{R2} .

$$V_{BE}=0.6396\text{V}$$

$$V_{CE}=1.3468\text{V}$$

$$V_{R1}=2.0312\text{V}$$

$$V_{R2}=1.9662\text{V}$$

$$I_{R1}=0.20312\text{mA}$$

$$I_{R2}=0.19662\text{mA}$$

$$I_B = I_{R1} - I_{R2} = 0.00650\text{mA} = 6.50\mu\text{A}$$

$$V_C = 1.3292\text{V}$$

$$I_C = 1.3292\text{mA}$$

$$V_E = 1.3320\text{V}$$

$$I_E = 1.3320\text{mA}$$

- 3) Verify that the circuit is in the forward active region.

We can see that we're in the forward active region because $V_{BE} \approx 0.7\text{V}$

- 4) For the present DC biasing, determine r_E using the equation $r_E = V_{\text{thermal}} / I_E$. Determine the common emitter current gain, $\beta = I_C / I_B$. Is the β value consistent with your previous determination of β (assuming that you are using the same transistor)? In your report, draw the small signal equivalent circuit of the DC bias circuit using the T-shaped and π -shaped BJT model.

$$r_E = V_{\text{thermal}} / I_E = 26\text{mV} / 1.3320\text{mA} = 19.51\Omega$$

$$\beta = I_C / I_B = 204.5$$

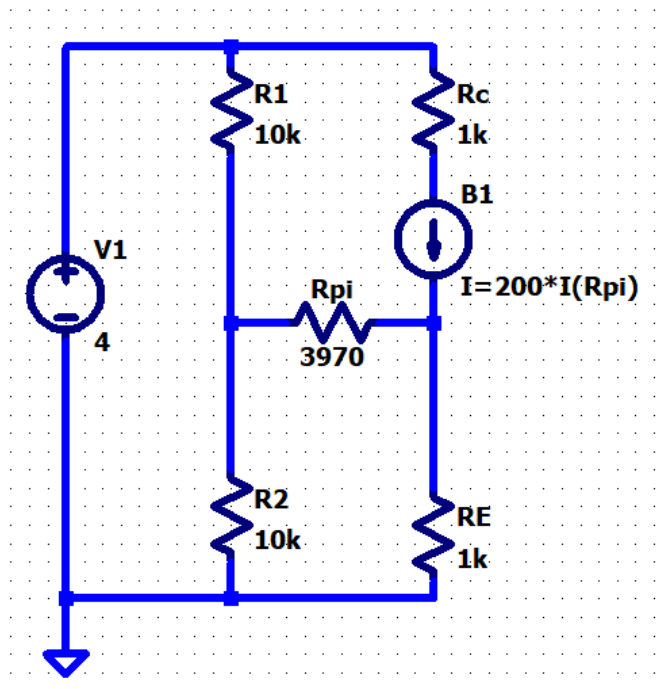
$$g = I_C / V_{\text{thermal}} = 1.3292\text{mA} / 26\text{mV} = 51.1\text{mS}$$

$$R_{\pi} = \beta / g = 200 / 51.1\text{mS} = 3970\Omega$$

$$a = \beta / (\beta + 1) = .995$$

$$R_E = .995 / g = 19.46\Omega$$

Pi:



T:

